

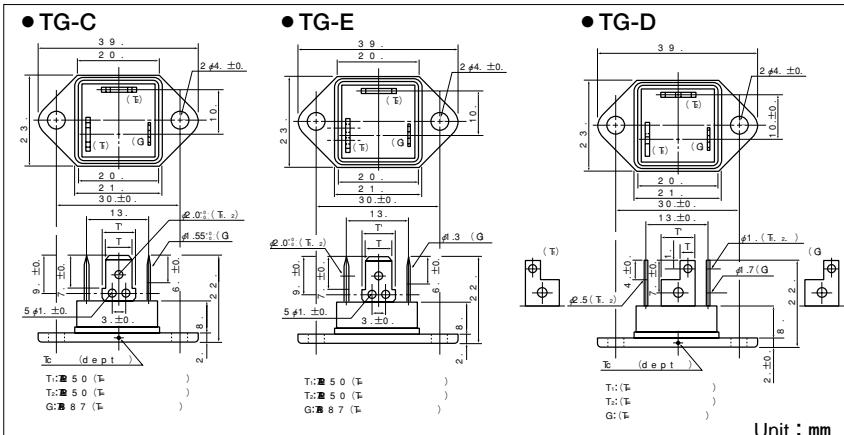
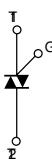
TRIAC (ISOLATED TYPE)

TG35C/E/D

UL:E76102(M)

TG35C/E/D are isolated molded triacs suitable for wide range of applications like copier, microwave oven, solid state switch, motor control, light control and heater control.

- $I_{T(AV)}$ 35A
- High surge capability 330A
- Isolated Nounting (AC2500V)
- Tab Terminals



Unit : mm

■ Maximum Ratings

($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Item	Ratings		Unit
		TG35C40	TG35C60	
V_{DRM}	Repetitive Peak Off-State Voltage	400	600	V
$I_{T(RMS)}$	R.M.S. On-State Current	35	A	
I_{TSM}	Surge On-State Current	300/330	A	
I^2t	I^2t	450	A^2s	
P_{GM}	Peak Gate Power Dissipation	10	W	
$P_{G(AV)}$	Average Gate Power Dissipation	1	W	
I_{GM}	Peak Gate Current	3	A	
V_{GM}	Peak Gate Voltage	10	V	
di/dt	Critical Rate of Rise of On-State Current	$I_G=100\text{mA}, T_j=25^\circ\text{C}, V_D=\frac{1}{2}V_{DRM}, di/dt=1\text{A}/\mu\text{s}$	50	$\text{A}/\mu\text{s}$
T_j	Operating Junction Temperature	$-25 \text{ to } +125^\circ\text{C}$		$^\circ\text{C}$
T_{stg}	Storage Temperature	$-40 \text{ to } +125^\circ\text{C}$		$^\circ\text{C}$
V_{iso}	Isolation Breakdown Voltage (R.M.S.)	2500	V	
	Mounting Torque (M4)	1.0-1.4(10-14)	1.5(15)	$\text{N}\cdot\text{m}$ (kgf·cm)
Mass	Typical value (Excluding bolt, nut and wrapping material)	23	g	

■ Electrical Characteristics

Symbol	Item	Conditions	Ratings	Unit
I_{DRM}	Repetitive Peak Off-State Current, max	$V_D=V_{DRM}$, Single phase, half wave, $T_j=125^\circ\text{C}$	5	mA
V_{TM}	Peak On-State Voltage, max	On-State Current [$\sqrt{2} \times I_{T(RMS)}$], Inst. measurement	1.4	V
I_{GT1}^+ 1	Gate Trigger Current, max	$T_j=25^\circ\text{C}, I_T=1\text{A}, V_D=6\text{V}$	50	mA
I_{GT1}^- 2		$T_j=25^\circ\text{C}, I_T=1\text{A}, V_D=6\text{V}$	50	
I_{GT3}^+ 3			—	
I_{GT3}^- 4		$T_j=25^\circ\text{C}, I_T=1\text{A}, V_D=6\text{V}$	50	
V_{GT1}^+ 1	Gate Trigger Voltage, max	$T_j=25^\circ\text{C}, I_T=1\text{A}, V_D=6\text{V}$	3	V
V_{GT1}^- 2		$T_j=25^\circ\text{C}, I_T=1\text{A}, V_D=6\text{V}$	3	
V_{GT3}^+ 3			—	
V_{GT3}^- 4		$T_j=25^\circ\text{C}, I_T=1\text{A}, V_D=6\text{V}$	3	
V_{GD}	Non-Trigger Gate Voltage, min	$T_j=125^\circ\text{C}, V_D=\frac{1}{2}V_{DRM}$	0.2	V
tgt	Turn On Time, max.	$I_{T(RMS)}, I_G=100\text{mA}, V_D=\frac{1}{2}V_{DRM}, T_j=25^\circ\text{C}, di/dt=1\text{A}/\mu\text{s}$	10	V
dv/dt	Critical Rate of Rise on-State Voltage,min.	$T_j=125^\circ\text{C}, V_D=\frac{2}{3}V_{DRM}$, Exponential wave.	20	$\text{V}/\mu\text{s}$
$(dv/dt)c$	Critical Rate of Rise off-State Voltage at commutation, min	$T_j=125^\circ\text{C}, V_D=\frac{2}{3}V_{DRM}$, $[di/dt] c=15\text{A}/\text{ms}$	5	$\text{V}/\mu\text{s}$
I_H	Holding Current, typ.	$T_j=25^\circ\text{C}$	30	mA
$R_{th(j-c)}$	Thermal Impedance, max	Junction to case	1.5	$^\circ\text{C}/\text{W}$

